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Raman Scattering Experiments on Unfilled Skutterudite CoSb₃ under High Pressure and High Temperature

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Abstract

In the present work, we study the anharmonicity of the unfilled CoSb₃ skutterudite from the pressure and temperature dependence of the Raman-active modes. A full assignment of the Raman-active modes of CoSb₃ was performed for the first time. Significant changes in the Raman spectrum are observed above 27 GPa and attributed to the insertion of antimony atoms within the cages under high external pressure. We report the lattice dynamics of SbCo₄Sb₁₂ by DFT calculations and find very low energy optical modes due to the antimony guest atoms with the cage framework. We report the isothermal Grüneisen parameters of the Raman-active modes, which are larger and approach 2 for the highest energy modes. From analysis of the temperature and pressure dependence of the Raman-active modes, we found that the implicit volume contribution is the dominant contribution for the highest energy Raman-active modes whereas both the implicit volume contribution and the explicit anharmonic contribution have same magnitude for the other Raman-active modes.

Keywords: thermoelectric, skutterudite, lattice dynamics

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I. Introduction

Skutterudite is a mineral discovered in Skutterud, Norway with the chemical formula $\text{Co}_{0.504}\text{Fe}_{0.21}\text{Ni}_{0.122}\text{Cu}_{0.184}\text{As}_{3.04}\text{S}_{0.05}$ and reported to have cubic symmetry by Oftedal.¹ Later on, it was shown that several compounds with the MX_3 chemical formula ($\text{M}=\text{Co}, \text{Rh}$ or Ir and $\text{X} = \text{pnictogen}$) have the same cubic symmetry with space group $\text{Im}-3$.²⁻⁶ The skutterudite structure MX_3 can be derived from the perovskite structure of ReO_3 by slightly tilting the octahedra formed by the oxygens. The stoichiometry of the skutterudite structure may be alternatively represented by its unit cell as $\square_2\text{M}_8\text{X}_{24}$ with the two voids corresponding to a (2a) Wyckoff site. It is then referred to as an unfilled skutterudite²⁻⁷ whereas with filled voids as in $\text{R}_2\text{M}_8\text{X}_{24}$ or RM_4X_{12} ($\text{R} = \text{rare-earth, alkaline-earth, alkaline metals, U, Th}$; $\text{M} = \text{Fe, Ru, Os}$ and $\text{X} = \text{pnictogen}$) it is called filled skutterudite.⁷⁻⁹ The physical properties of unfilled skutterudites were first studied in the 1950s and studies were very few until the 1980s.¹⁰⁻¹² They suggested that some of those compounds are narrow-gap semiconductors with some potential for thermoelectric applications.¹⁰⁻¹² During the 1980s, infrared studies confirmed the semiconducting character of many skutterudites, outlined their vibrational properties¹³⁻¹⁵ and a more accurate study of the crystal structure of CoSb_3 was performed.¹⁶ In the middle of 1990s, the potential of the unfilled skutterudites for thermoelectricity was rediscovered.¹⁷⁻²¹ Filled skutterudites were studied for the first time and found to be promising for thermoelectric applications.²²⁻²⁴ The performance of thermoelectric materials is characterized by the dimensionless figure of merit $ZT = \sigma\alpha^2T/\kappa$, where σ is the electrical conductivity, α is the Seebeck coefficient, T is the temperature and κ is the thermal conductivity which has a lattice contribution κ_l and an electron contribution κ_e .^{7,25} The most widely used commercial thermoelectric materials are alloys based on Bi_2Te_3 and on PbTe with ZT of about 1.²⁵ The best ZT for the p-type skutterudites was found to be around 1.4 at 600°C for the filled skutterudite $\text{CeFe}_{3.5}\text{Co}_{0.5}\text{Sb}_{12}$ ²⁴ whereas the best ZT for the n-type skutterudites was found around 1.7-1.9 at 550°C for the partially multi-filled skutterudite $(\text{R}, \text{R}', \text{R}'')\text{Co}_4\text{Sb}_{12}$.^{26,27} Recently, the thermoelectric properties of n-type unfilled skutterudite CoSb_3 have been improved with tellurium doping ($ZT = 1.1$ at 550°C)²⁸ and with tellurium and silicon codoping together with significant porosity ($ZT = 1.6$ at 550°C).²⁹ The most promising n-type skutterudite compound for thermoelectric applications is thus CoSb_3 ^{7,26-29} and in

addition it is made of more abundant and less toxic elements than other skutterudites. CoSb_3 is a narrow-gap semiconductor with an indirect bandgap and its valence band has linear dispersion.³⁰⁻³¹ Recent studies indicate the possibility of a conventional to topological phase transition.³²⁻³³ There is no clear consensus about the experimental value of the indirect bandgap whereas the optical direct bandgap was recently found to be 0.23 eV.³⁴ DFT calculations are well known to underestimate the bandgap of materials.^{35,36} In the case of CoSb_3 , only recently more accurate calculations using meta-Generalized Gradient Approximation (meta-GGA) exchange-correlation functional or GW method were reported.³⁷ From these methods, the indirect bandgap is about 0.33 eV.³⁷ The knowledge of the lattice dynamics of thermoelectric materials is a fundamental step to understand their thermal conductivity. In a previous work, we have shown that the vibrations of the guest atoms in the filled skutterudites form proper eigenmodes with the host-lattice.³⁸ They are of appreciably low energy which is a fundamental feature for explaining their low thermal conductivity.³⁹⁻⁴² Concerning CoSb_3 , its lattice dynamics was studied by Infrared spectroscopy,¹³⁻¹⁵ Raman spectroscopy,⁴³⁻⁴⁵ inelastic neutron scattering,⁴⁶ inelastic and resonant X-ray scattering^{47,48} as well as by harmonic⁴⁹⁻⁵¹ and anharmonic^{40,52,53} DFT and molecular dynamics calculations.^{51,54} However, so far neither the mode Grüneisen parameters nor experimental data of the anharmonicity of the lattice dynamics of CoSb_3 have been reported, which are of fundamental importance for a good understanding of the phonon scattering mechanisms in the thermal conductivity. Raman experiments under pressure have been recently performed on another unfilled skutterudite CoP_3 and its mode Grüneisen parameters were obtained.⁵⁵ Also, the effect of pressure on the guest mode of $\text{LaFe}_4\text{Sb}_{12}$ was recently calculated by Martinotto *et al.*⁵⁶ Moreover, a recent theoretical work has reported an improvement of the thermoelectric properties of CoSb_3 under high pressure.⁵⁷ Several studies have discussed the effect of pressure on the crystal structure of CoSb_3 and reported the equation of states and the bulk modulus of CoSb_3 and other skutterudites.⁵⁸⁻⁶⁵ They also reported an antimony insertion reaction under high external pressure in the antimonide and arsenide unfilled skutterudites above 20 GPa at room temperature⁶⁰⁻⁶⁵ and at pressures lower than 10 GPa under high pressure-high temperature (HP-HT) conditions.^{64,65} Until now, only thermoelectric and transport properties of these $\text{Sb}_x\text{Co}_4\text{Sb}_{12-x}$ samples were studied.⁶⁵ Other properties such as lattice dynamics under high pressure of CoSb_3 are missing.

The aim of the present work is to study CoSb_3 by Raman spectroscopy under high pressure and high temperature. This will permit to determine the mode Grüneisen parameters, the different contributions of the anharmonicity as well as the effect of the antimony insertion reaction under high external pressure on the dynamics of the compound. In addition, we have computed the lattice dynamics of $\text{SbCo}_4\text{Sb}_{12}$ in order to approximate the dynamics of the antimony guests.

II. Methods

The polycrystalline CoSb_3 sample used for the high-pressure experiments was obtained by using pieces of antimony and cobalt placed in stoichiometric amount in a carbon-coated quartz tube. This was heated at 1050°C for 48 h, then cooled down to 900°C at 6°C/h , then to 800°C at 15°C/h and finally to room temperature at 100°C/h . X-ray diffraction confirmed that the majority phase is CoSb_3 (76 %) and show the presence of significant amounts of antimony (24 %). See the Supplementary Information for the details. The single-crystals of CoSb_3 were obtained using the iodine transport method in a gradient furnace. SbI_3 was used as agent for the chemical transport. We have performed single-crystal X-ray diffraction on one piece cut from a crystal and confirmed that we have obtained single-crystals of CoSb_3 of good quality. See the Supplementary Information for the details. The atomic positions are reported in Table 1.

Raman scattering experiments under high pressure were performed using a Raman spectrometer equipped with Peltier cooled CCD and with a green laser ($\lambda = 532 \text{ nm}$). The spectral resolution is about $1\text{-}2 \text{ cm}^{-1}$. High-pressure measurements were performed within a membrane diamond anvil cell (DAC) with low fluorescence diamonds. The samples were placed into a $100 \text{ }\mu\text{m}$ chamber drilled in an indented stainless-steel gasket. The pressure transmitting medium was dense argon that has no Raman signal. Solid Ar is extremely compressible and provides nearly quasi-hydrostatic conditions.⁶⁶ The fluorescence of ruby was used as a pressure gauge.⁶⁷ The pressure error is estimated to about 0.1 GPa. Care has been done to avoid the presence of antimony in our experiments. See below for a discussion. Raman scattering experiments above room T were performed with a Horiba Jobin-Yvon Labram Aramis spectrometer equipped with Peltier cooled CCD and a He-Ne laser ($\lambda = 633 \text{ nm}$). The spectral resolution of the experiment is about 1 cm^{-1} . The high temperature experiments were performed in the oven of a

Linkham TS15000 heating stage under the objective (X50) of an Olympus microscope. The temperature was measured with a Pt resistance at the bottom of the oven. The temperature error is estimated to about 10 °C at the highest temperature.

In all the Raman experiments, the spectra were obtained in a backscattering configuration using a microscope device that allows the incident light to be focused on the sample as a spot of several micrometers diameter.

The Density Functional Theory (DFT) calculations were based on Projector Augmented Wave (PAW) pseudopotentials and the Perdew-Burke-Ernzerhof (PBE) exchange-correlation functional using the Vienna *ab initio* Simulation Package (VASP).^{68,69} For all calculations, an energy cut-off of 350 eV was applied, the force convergence was 10^{-5} eV/Å and the energy convergence was 10^{-10} eV. We applied a k-meshes of 11x11x11 for both $\square\text{Co}_4\text{Sb}_{12}$ (CoSb_3) and $\text{SbCo}_4\text{Sb}_{12}$. The relaxed lattice parameters found are 9.11043 Å for $\square\text{Co}_4\text{Sb}_{12}$ and 9.1865 Å for $\text{SbCo}_4\text{Sb}_{12}$, thus the intercalation of Sb guest atoms at the (2a) site increases the lattice parameter by about 0.8 %. The space group is Im-3 for both compounds, as in the experiments.^{5,16,21,68,70} The experimental values of the lattice parameter of $\square\text{Co}_4\text{Sb}_{12}$ at room temperature are between 9.016 Å and 9.0385 Å in the literature,^{5,16,21,70} whereas one finds 9.0369(3) Å for the case of our single-crystal and 9.03890(6) Å for our polycrystals. This can be compared to the lattice parameter of 9.129 Å for $\text{Sb}_{0.8}\text{Co}_4\text{Sb}_{11.2}$ obtained by HP-HT synthesis,⁶⁸ which corresponds to an increase of 1 % to 1.25 %. By comparison with our calculations, one can conclude that the Sb vacancies have only little effect on the volume. The positions of the atoms calculated for $\square\text{Co}_4\text{Sb}_{12}$ and $\text{SbCo}_4\text{Sb}_{12}$ are reported in Tables 1 and 2. The positions of the Sb atoms of the framework are slightly different from the experiments⁶⁵ and change slightly between $\square\text{Co}_4\text{Sb}_{12}$ and $\text{SbCo}_4\text{Sb}_{12}$. We also note that in the experiments, the Sb_{guest} atoms are off-centered⁶⁵ while they are on-centered in the calculations. This could be due to the presence of Sb vacancies in the experiments. We have calculated the curve of energy vs volume of $\square\text{Co}_4\text{Sb}_{12}$ at different constant volumes and fitted it with the Vinet equation.⁷¹ We found a bulk modulus of $B = 83$ GPa and a pressure derivative of $\text{dB}/\text{dP} = 6.3$. The bulk modulus is close to the experimental values found by Shirotani *et al* using the Birch-Murnaghan equation ($B = 81$ GPa and $\text{dB}/\text{dP} = 6.1$)⁵⁸ but much smaller than the value found by Kraemer *et al* using the Vinet equation ($B =$

97.1 GPa and $dB/dP = 4$)⁵⁹ or by Kraemer *et al* using the Birch-Murnaghan equation ($B = 93$ GPa and $dB/dP = 5$).⁶⁰

Lattice dynamics calculations were carried out with the direct method from the Hellmann-Feynman (HF) forces computed on the relaxed skutterudite structures. The HF forces were derived by displacing atoms from their equilibrium positions by 0.03 Å along non-equivalent high-symmetry directions. The lattice dynamics properties were computed from the HF forces by the diagonalization of the dynamical matrix with the software package Phonon.⁷² For calculating the mode Grüneisen parameters $\gamma_i = -d \ln \omega_i / dV$, we calculated the mode frequencies ω_i for different volumes V .

In the present calculations, the spin-orbit coupling (SOC) has not been included. However, for heavy atoms like Bi or Tl, the SOC is not negligible.⁷³ The SOC will affect less the Sb because it is much lighter than these atoms. Indeed, Haussermann *et al* was able to accurately describe Sb under pressure with the different transitions to the high pressure Sb phases without taking into account the SOC.⁷⁴ This means that the effect of SOC for Sb is small. Among all DFT calculations performed for CoSb₃, only Smith *et al*³² have examined the case of the SOC. They studied the effect of both tetragonal distortion and SOC. They found that the effect SOC is small, but when coupled to a tetragonal distortion, it opens the gap required to give a topological insulator. Note however that the calculations were performed using a GGA exchange-correlation functional as in the later study of the same group,³³ which underestimates the bandgap of CoSb₃ as Khan *et al*³⁷ have shown.

III. Results

In the unfilled skutterudite CoSb₃, there are 16 atoms in the primitive unit cell and therefore 48 different vibrational modes with 3 acoustic and 45 optic modes. The presentation in an irreducible decomposition of the optic modes is the following:

$$\Gamma = 2 A_g \oplus 2 E_g \oplus 4 T_g \oplus 2 A_u \oplus 2 E_u \oplus 7 T_u$$

The modes with A_g , E_g and T_g symmetries are Raman-active and thus there are 8 Raman-active modes.

The 7 modes with T_u symmetry are infrared-active modes. In the case of the filled skutterudites

$\text{RCo}_4\text{Sb}_{12}$, the R guest atom located on the (2a) site and the corresponding additional mode has T_u symmetry and there are therefore 8 infrared-active modes.

We report in Fig. 1 the Raman spectrum of the single-crystal sample. The energies of the Raman-active modes are listed in Table 3. The results are in good agreement with the most recent Raman scattering experiments.⁴⁵ We notably confirm the doublet at 175 cm^{-1} found in this last work and which was not observed before.^{43,44} In addition, based on our Raman scattering experiments at high temperature (see below), we were able to show that the asymmetry of the peak at about 150 cm^{-1} is due to the presence of two Raman-active modes of A_g and T_g symmetries, in very good agreement with our DFT calculations (see Tables 3 and 4) and prior lattice dynamics calculations using force constant models⁴⁹ and DFT.^{47,50} Therefore, in the present work, we are able to assign the 8 Raman active modes of CoSb_3 for the first time. The full-width at half-maximum (FWHM) Δ_i vary between 1.3 cm^{-1} and 3.7 cm^{-1} , which corresponds to relaxation time τ_i between 1.4 ps and 4.1 ps. These values are in good agreement with the relaxation rates of 0.03 to 0.1 THz, i. e. 1 cm^{-1} to 3.3 cm^{-1} , found by Li and Mingo for the optical phonons between 80 cm^{-1} and 200 cm^{-1} by anharmonic ab initio calculations on CoSb_3 .⁵²

The thermal variation of the mode frequencies is divided into two contributions:^{75,76}

$$\omega_i(T) = \omega_i(T = 0 \text{ K}) + \Delta\omega_i^{\text{impl}} + \Delta\omega_i^{\text{expl}}$$

Where $\Delta\omega_i^{\text{impl}}$ is the implicit contribution taking into account the volume dependence of the mode frequencies and $\Delta\omega_i^{\text{expl}}$ is the explicit contribution determined by the thermal population of the vibrational levels and depending on the anharmonicity.

In the harmonic approximation, the frequencies of the vibrational modes are constants and do not change with volume, pressure or temperature. In the quasi-harmonic approximation, the frequencies of the vibrational modes vary with the volume change and therefore with the temperature and pressure. Thus, in the Grüneisen approximation, this can be expressed as:

$$\frac{\omega_i}{\omega_i(T = 0 \text{ K})} = \left(\frac{V}{V_0}\right)^{-\gamma_i}$$

with ν_i the i^{th} mode frequency, $\nu_i(T=0 \text{ K})$ the i^{th} mode frequency at $T = 0 \text{ K}$, V the cell volume, V_0 the cell volume at $T = 0 \text{ K}$ and γ_i the i^{th} mode Grüneisen parameter.

One can define the isothermal Grüneisen parameter γ^T and the isobaric Grüneisen parameter γ^P of the i^{th} mode as:⁷³

$$\gamma_i^T = \left(\frac{\partial \ln \omega_i(P,T)}{\partial \ln(V(P,T))} \right)_T \text{ and } \gamma_i^P = \left(\frac{\partial \ln \omega_i(P,T)}{\partial \ln(V(P,T))} \right)_P.$$

In the isotropic approximation, they can also be expressed as:^{75,76}

$$\gamma_i^T = B \left(\frac{\partial \ln \omega_i}{\partial P} \right)_T \text{ and } \gamma_i^P = \frac{-1}{\alpha_V} \left(\frac{\partial \ln \omega_i}{\partial T} \right)_P$$

with B being the bulk modulus and α_V being the volume thermal expansion.

The thermal variation of the frequency can be determined as:^{75,76}

$$\left(\frac{\partial \omega_i}{\partial T} \right)_P = -B \alpha_V \left(\frac{\partial \omega_i}{\partial P} \right)_T + \left(\frac{\partial \omega_i}{\partial T} \right)_V$$

One can express this equation as:⁷⁶

$$\gamma_i^P = \gamma_i^T + \gamma_i^V$$

with $\gamma_i^V = \frac{-1}{\alpha_V} \left(\frac{\partial \ln \omega_i}{\partial T} \right)_V = -B \left(\frac{\partial \ln \omega_i}{\partial P} \right)_V$.

Based on Raman scattering experiments under high pressure, one can determine the isothermal Grüneisen parameters γ_i^T and by Raman experiment as a function of temperature, one can determine the isobaric Grüneisen parameters γ_i^P . If the quasi-harmonic approximation can be strictly applied, $\gamma_i^V = 0$ and $\gamma_i^P = \gamma_i^T$. Therefore, in the general case, γ_i^V is a measure of the anharmonic contribution to the frequency shift, i. e. the explicit effect, whereas γ_i^T corresponds to the volume contribution, i. e. the implicit effect. One can thus define the implicit fraction $\eta_i = \gamma_i^T / \gamma_i^P$.⁷⁶

We have performed Raman scattering experiments to study the self-intercalation of antimony under high pressure as reported using X-ray diffraction by prior studies⁶⁰⁻⁶⁵ and to determine the Grüneisen parameters γ_i^T of the different Raman-active modes. As the experiments have been performed on a polycrystalline sample the Raman spectra of which exhibit larger FWHM values. We are therefore not able to distinguish neither the two Raman-active modes around 150 cm^{-1} nor the two Raman modes around 175 cm^{-1} . Unfortunately, we were not able to observe the T_g Raman-active mode at about 80 cm^{-1} . The Raman spectra as function of pressure are shown in Fig. 2 for two different runs. Because of the presence of antimony in our polycrystalline sample, one can ask if our Raman spectra of the

polycrystalline samples under pressure are contaminated by the signal of antimony. In the Raman signal of antimony, there are two intense peaks at 112.5-115 cm^{-1} and 150-153 cm^{-1} ^{43,77} and H. Olijnyk et al have shown that their frequency positions decrease significantly with increasing pressure, ⁷⁷ in contrast with our results where the frequency positions of all the Raman modes increase significantly with increasing pressure. This means that there is no antimony in the zone of the samples studied in our experiments. At 27 GPa, the Raman peaks are suddenly broadened. This spectral change is thought to be due to a structure change. Since the spectral shapes of the high pressure phase are similar to those of filled skutterudite, ⁴⁵ the phase change can be interpreted according to self insertion of Sb proposed by Kraemer *et al.* ^{59,60} This structure change at 27 GPa is found to be irreversible because after pressurization to 36 GPa the spectrum is not recovered when decompressing down to room pressure (see Supplementary Information). We obtained a spectrum with two broad peaks at 150 cm^{-1} and 175 cm^{-1} . We also note that there was an irreversibility of the volume change after decompression in the XRD experiments done by Kramer et al ⁶⁰ and Matsui et al. ^{61,63} Using DFT calculations, we have checked that moving one Sb atom from the cage framework to the (2a) site is unstable both at 0 and 30 GPa. This suggests that the structure change could be just a structural instability. The Sb-vacancies and Sb-guests could be kinetically trapped after decompression. However, further studies are required to confirm this scenario.

In order to understand the effect of the intercalation of Sb guest atom on the (2a) site on the lattice dynamics, we have performed DFT calculations of $\text{SbCo}_4\text{Sb}_{12}$ at 0 GPa and 30 GPa. The phonon dispersion curves and phonon density of states of $\text{SbCo}_4\text{Sb}_{12}$ and of CoSb_3 (for comparison) at 0 GPa are presented in Figs 3 and 4, respectively. We list the Γ point frequencies of $\text{SbCo}_4\text{Sb}_{12}$ in Table 5. The incorporation of Sb guest atom downshifts significantly the vibration modes. This is mainly due to the expansion of the lattice by the intercalation of the Sb guest atom. A similar behaviour has been observed in Raman scattering experiments of $\text{Sn}_x\text{Co}_4\text{Sb}_{12}$, however, with much lower magnitude. ⁴⁵ As expected, we also find that there is an additional T_u infrared-active mode due to the Sb guest atom at the (2a) site at 35.8 cm^{-1} . We note that the characteristic frequencies of vibrations between 30 and 50 cm^{-1} are connected to both the Sb guest atom and the Sb atoms of the cage framework.

We have calculated the atomic displacement parameters (ADPs) of the different atoms (see Supplementary Information). As expected, we find a much larger ADP for the Sb guest atoms located at the (2a) site. At 300 K, we find $B_{\text{iso}}(\text{Co}) = 0.42 \text{ \AA}^2$, $B_{\text{iso}}(\text{Sb}) = 0.67 \text{ \AA}^2$ and $B_{\text{iso}}(\text{Sb}_{\text{guest}}) = 2.02 \text{ \AA}^2$. These values are in reasonable agreement with the values found for $\text{Sb}_{0.8}\text{Co}_4\text{Sb}_{11.2}$: $B_{\text{iso}}(\text{Co}) = 0.8(6) \text{ \AA}^2$, $B_{\text{iso}}(\text{Sb}) = 0.8(7) \text{ \AA}^2$ and $B_{\text{iso}}(\text{Sb}_{\text{guest}}) = 2.2(3) \text{ \AA}^2$.⁶⁵ Upon increasing the pressure to 30 GPa, all vibrational modes have positive frequencies, indicating that $\text{SbCo}_4\text{Sb}_{12}$ is a stable structure. At this pressure, the atom-projected phonon DOS of the Sb guest atoms is greatly upshifted up to 65 cm^{-1} and the low energy vibrational modes are dominated by the Sb atoms of the framework up to 100 cm^{-1} (see Supplementary Information). As the Sb guest atoms give an additional IR T_u mode, we cannot see it in Raman experiments and our calculations predict that the signature of the Sb intercalation in the Raman scattering should be the downshift of the Raman-active mode after decompression down to room pressure. However, because of the large broadening of the peak, this is difficult to confirm.

Fig. 5 shows the pressure dependence of Raman frequencies of CoSb_3 . The error of the Raman frequencies are within the size of the symbols. The isothermal mode Grüneisen parameters γ_i^T are listed in Table 3. The pressure dependence of the cell volume, which is needed for obtaining the γ_i^T , was taken from Kraemer *et al.*⁶⁰ We report the isothermal mode Grüneisen constants γ_i^T from the DFT calculations in Tables 3 and 4. There is a good correspondence with the experimental values. The three lowest energy vibrational modes have low γ_i^T values, which are less than 1. These values can be compared to the thermodynamic Grüneisen parameter $\Gamma = 3 \alpha V B / C_P$, where α is the linear thermal expansion, V the molar volume and C_P the heat capacity.⁷⁸ Caillat *et al* reported that $\alpha = 6.36 \text{ MK}^{-1}$ and that the Grüneisen parameter $\Gamma = 0.952$.⁷⁹ However, two recent works reported a thermal expansion that was 50 % larger.^{80,81} Using $\alpha = 9.9 \text{ MK}^{-1}$ found by Hanus *et al*,⁸¹ one derives $\Gamma = 1.482$. This value is intermediate between the different mode Grüneisen parameters γ_i^T found above.

We show the Raman spectra of single-crystal CoSb_3 as a function of temperature in Fig. 6. Note that besides the downshift of the different peaks, the peak at about 150 cm^{-1} splits into two peaks with increasing temperature. This shows that the slightly asymmetric peak at about 150 cm^{-1} has two different components (see above for more detailed explanations). Conversely, the two peaks at about 175 cm^{-1}

merge into one asymmetric peak with increasing temperature. We report the thermal variation of the positions of the different Raman-active modes in Fig. 7(a). The error of the mode positions are within the size of the symbols. As the mode positions vary linearly with the temperature from room temperature up to 400°C (except for the two highest energy T_g modes), one can determine the isobaric Grüneisen parameters γ_i^P from the slope obtained by linear fitting of the thermal variation of the frequencies and with the knowledge of the thermal expansion obtained by Hanus *et al.*⁸¹ From the knowledge of both γ_i^P and γ_i^T , one can obtain γ_i^V and the implicit ratio η_i of each Raman-active mode. The results are given in Table 3. For the lowest energy A_g and E_g modes and for the T_g mode at about 108 cm^{-1} , the ratio η_i is about 0.5, which means that the implicit volume contribution and the explicit anharmonic contribution are more or less the same. However, for the two highest energy modes, the ratio η_i is larger than 0.5, which means that the implicit volume contribution is the dominant component. When η_i is smaller than or about 0.5, the bonding is covalent, like in ZnS or semiconducting Mg_2X ($\text{X} = \text{Si}, \text{Ge}, \text{Sn}$) and when it is significantly larger than 0.5, the bonding is ionic.⁸²⁻⁸⁴ In the case of CoSb_3 , we have both cases, which means that the bonding is iono-covalent.

We show the thermal variation of the FWHM Δ_i of the lowest E_g and the highest A_g mode in Fig. 7(b). We notice a clearly increasing trend with increasing temperature. It is difficult to deconvolute the two modes at 150 cm^{-1} and 175 cm^{-1} and to derive reliable FWHM Δ_i without large errors. The same holds for the peak of the lowest energy T_g mode due to its very low intensity.

The FWHM Δ_i can be expressed as function of the residual term $\Delta(0)$ of the 3 phonons interaction term Δ_3 and of the 4 phonons interaction term Δ_4 :^{75,76,85}

$$\Delta_i = \Delta (T = 0 \text{ K}) + \Delta_3 + \Delta_4$$

With the term $\Delta (T = 0 \text{ K})$ being constant and:^{75,76,85}

$$\Delta_3 = A \left(1 + \frac{2}{e^x - 1} \right) \text{ and } \Delta_4 = B \left[1 + \frac{3}{e^y - 1} + \frac{3}{(e^y - 1)^2} \right]$$

$$\text{with } x = \frac{\hbar\omega_i}{2k_B T} \text{ and } y = \frac{\hbar\omega_i}{3k_B T}.$$

The experimental data were modeled using these equations in Figure 7 (b).

IV. Conclusion

We have reported a study of the anharmonicity of the unfilled skutterudite CoSb_3 from the pressure and temperature dependence of the Raman-active modes. Based on the temperature dependence, we were able to carry out the full assignment of the Raman-active modes of CoSb_3 for the first time. We have observed a significant broadening and irreversible change of the Raman spectrum above 27 GPa. This was attributed to the self-insertion of antimony atoms in the cages, which was reported in some prior structural studies of CoSb_3 under high pressure.⁶⁰⁻⁶³ We reported the lattice dynamics of $\text{SbCo}_4\text{Sb}_{12}$ by DFT calculations and find a very low energy optical mode due to the formation of hybrid modes of the guest atoms with the host network. We reported the isothermal Grüneisen parameters of the Raman-active modes that are as large as 2 for the highest energy modes. From the analysis of the thermal and pressure dependence of the Raman-active modes, we found that the implicit volume contribution is the dominant contribution for the highest energy Raman-active modes, whereas both implicit volume contribution and explicit anharmonic contribution have same magnitudes for the other Raman-active modes.

V. Associated content

V. A. Supplementary informations

Raman spectra of CoSb_3 under decompression, calculations of the atomic potential of silicon in $\text{Ba}_{24}\text{Si}_{100}$, the calculations of the electronic density of states of CoSb_3 and $\text{SbCo}_4\text{Sb}_{12}$ at 0 GPa, the calculations of the atomic displacements parameters of $\text{SbCo}_4\text{Sb}_{12}$ at 0 GPa, the calculations of the phonon dispersion curves and density of states $\text{SbCo}_4\text{Sb}_{12}$ at 30 GPa.

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Table captions

Table 1 : Atomic positions of CoSb_3 from the single-crystal and powder X-ray diffraction experiments and from DFT calculations.

Table 2 : Atomic positions of $\text{SbCo}_4\text{Sb}_{12}$ from the DFT calculations.

Table 3 : Eigenenergies (in cm^{-1}), FWHM (in cm^{-1}), relaxation time (in ps) and Grüneisen parameters of the Γ point modes of CoSb_3 from the Raman scattering experiments. Eigenenergies (in cm^{-1}) and Grüneisen parameters of the Γ point Raman active modes of CoSb_3 from the DFT calculations.

Table 4 : Eigenenergies (in cm^{-1}) and Grüneisen parameters of the Γ point modes of CoSb_3 from the DFT calculations.

Table 5 : Eigenenergies (in cm^{-1}) of the Γ point modes of $\text{SbCo}_4\text{Sb}_{12}$ at 0 GPa and 30 GPa from the DFT calculations.

Tables

Atom	site	x	y	z	Comments
Co	8c	$\frac{1}{4}$	$\frac{1}{4}$	$\frac{1}{4}$	Experiments and DFT
Sb	24g	0	0.33510(2)	0.15787(2)	Single-crystal
		0	0.33485(11)	0.15750(12)	Powder
		0	0.333449	0.159027	DFT

Table 1

Atom	site	x	y	z
Co	8c	$\frac{1}{4}$	$\frac{1}{4}$	$\frac{1}{4}$
Sb	24g	0	0.330514	0.15913
Sb _{guest}	2a	0	0	0

Table 2

Symmetry	ω_i (cm ⁻¹)	ω_i (cm ⁻¹)	Δ_i (cm ⁻¹)	τ_i (ps)	γ_i^T	γ_i^T	γ_i^P	γ_i^V	η_i
	exp.	DFT	exp.	exp.	exp.	DFT	exp.	exp.	exp.
A _g	149.5	145.1	1.3	4.1	1.85	1.89	3.24	1.39	0.57
	177.8	174.3	1.9	2.8	1.64	1.68	2.34	0.7	0.7
E _g	134	126.8	2.1	2.5	1.64	1.64	3.44	1.8	0.48
	185.2	179.7	2	2.65	1.87	1.8	2.45	0.58	0.76
T _g	81.5	80.2	3.7	1.4		0.3			
	108.4	102.4	2.5	2.1	1.28	1.23	2.41	1.13	0.53
	150.6	145.5	2.7	2		1.89			
	174.8	171	3.7	1.4		1.8			

Table 3

Symmetry	ω_i (cm ⁻¹)	γ_i^T
A _g	145.1	1.89
	174.3	1.68
E _g	126.8	1.64
	179.7	1.8
T _g	80.2	0.3
	102.4	1.23
	145.5	1.89
	171	1.8
A _u	110.4	0.44
	240.6	1.84
E _u	127.1	0.77
	251.4	2.09
T _u	75.8	0.75
	114.7	1.29
	137.6	1.58
	171	1.5
	233.9	1.8
	243.7	1.71
	259.5	1.9

Table 4

Symmetry	P = 0 GPa	P = 30 GPa
A _g	133.6	203.3
	162.8	226.4
E _g	103.4	169.1
	163.4	235.8
T _g	67.5	77.3
	98.2	124.9
	138.3	198.3
	164.3	231.5
A _u	103.6	110.4
	228.9	331.1
E _u	118.2	137.4
	237.9	353.1
T _u	35.8	64.9
	74.5	117.3
	101	141.3
	110.1	157
	156.1	212.6
	219.1	314.3
	227.5	328.9
	244.3	357.2

Table 5

Figure captions

Figure 1: Experimental Raman spectrum of a CoSb₃ single crystal at T = 24 °C.

Figure 2: Evolution of the Raman spectra of CoSb₃ upon compression. Two different runs are shown.

Figure 3: Phonon dispersion curves of (a) CoSb₃ and (b) SbCo₄Sb₁₂ from DFT calculations.

Figure 4: Total and atom-projected phonon density of states of SbCo₄Sb₁₂ from DFT calculations.

Figure 5: Variation of the frequencies of some Raman-active modes in CoSb₃ with pressure. Full circles are the experimental data; open symbols are the DFT data with T_g symmetry (red circles), E_g symmetry (blue triangles) and A_g symmetry (black squares).

Figure 6: Evolution of the Raman spectra modes of CoSb₃ with temperature.

Figure 7: (a) Variation of the frequencies of the Raman-active modes in CoSb₃ with temperature. Mode symmetries are given in the figure. (b) Variation of the FWHM of the Raman-active E_g modes in CoSb₃ with temperature. Experimental data are represented as symbols, calculations with 3 phonon and 4 phonon interactions as solid lines.

Figures

Figure 1

Figure 2

Figure 3

Figure 4

Figure 5

Figure 6

Figure 7

TOC graphic